MMBV3102LT1

Preferred Device

Silicon Tuning Diode

This device is designed in the Surface Mount package for general frequency control and tuning applications. It provides solid–state reliability in replacement of mechanical tuning methods.

Features

- High Q with Guaranteed Minimum Values at VHF Frequencies
- Controlled and Uniform Tuning Ratio
- Pb–Free Package is Available

MAXIMUM RATINGS ($T_C = 25^{\circ}C$ unless otherwise noted)

Rating	Symbol	Value	Unit
Reverse Voltage	V _R	30	Vdc
Forward Current	١ _F	200	mAdc
Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	225 1.8	mW mW/°C
Junction Temperature	TJ	+125	°C
Storage Temperature Range	T _{stg}	-55 to +150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.



ON Semiconductor®

http://onsemi.com







MARKING DIAGRAM



M4C = Specific Device Code M = Date Code* Pb-Free Package (Note: Microdot may be in either location) *Date Code orientation and/or overbar may

vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBV3102LT1	SOT-23	3,000 / Tape & Reel
MMBV3102LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

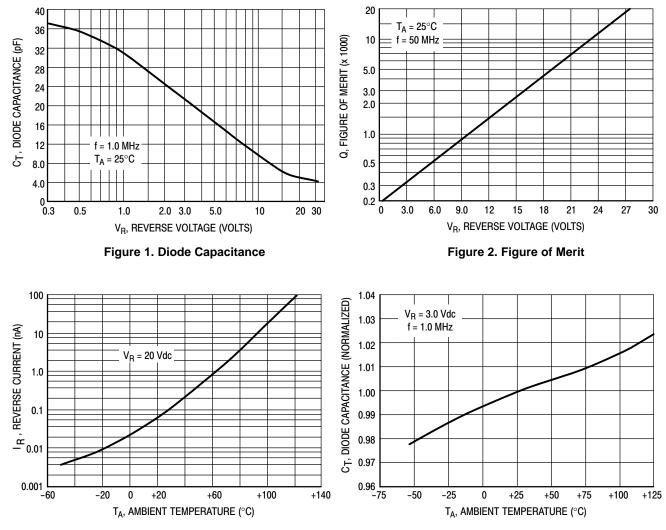
Preferred devices are recommended choices for future use and best overall value.

MMBV3102LT1

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
Reverse Breakdown Voltage (I _R = 10 μAdc)	V _{(BR)R}	30	-	-	Vdc
Reverse Voltage Leakage Current ($V_R = 25 \text{ Vdc}, T_A = 25^{\circ}\text{C}$)	I _R	-	-	0.1	μAdc
Diode Capacitance Temperature Coefficient $(V_R = 4.0 \text{ Vdc}, f = 1.0 \text{ MHz})$	тс _с	-	300	-	ppm/°C

	C _t , Diode Capacitance V _R = 3.0 Vdc, f = 1.0 MHz pF		Q, Figure of Merit $V_R = 3.0 \text{ Vdc}$ f = 50 MHz	C _R , Capacitance Ratio C ₃ /C ₂₅ f = 1.0 MHz		
Device	Min	Nom	Max	Min	Min	Тур
MMBV3102LT1	20	22	25	200	4.5	4.8



TYPICAL CHARACTERISTICS

Figure 3. Leakage Current

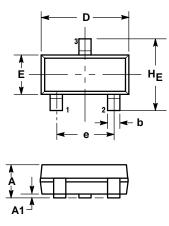
Figure 4. Diode Capacitance

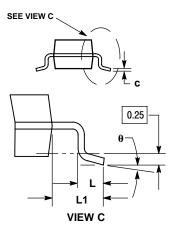
NOTES ON TESTING AND SPECIFICATIONS

1. C_R is the ratio of C_T measured at 3.0 Vdc divided by C_T measured at 25 Vdc.

PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 ISSUE AN





NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
 MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISLITUICKNESS MINIMUM EAD
- FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- BASE MATERIAL.
 4. 318–01 THRU –07 AND –09 OBSOLETE, NEW STANDARD 318–08.

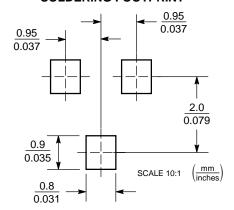
	MILLIMETERS			INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.89	1.00	1.11	0.035	0.040	0.044	
A1	0.01	0.06	0.10	0.001	0.002	0.004	
b	0.37	0.44	0.50	0.015	0.018	0.020	
С	0.09	0.13	0.18	0.003	0.005	0.007	
D	2.80	2.90	3.04	0.110	0.114	0.120	
E	1.20	1.30	1.40	0.047	0.051	0.055	
е	1.78	1.90	2.04	0.070	0.075	0.081	
L	0.10	0.20	0.30	0.004	0.008	0.012	
L1	0.35	0.54	0.69	0.014	0.021	0.029	
HE	2.10	2.40	2.64	0.083	0.094	0.104	

STYLE 8:

PIN 1. ANODE

NO CONNECTION
 CATHODE

SOLDERING FOOTPRINT*



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and use registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other application in which the failure of the SCILLC product create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use personal and subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 61312, Phoenix, Arizona 85082–1312 USA Phone: 480–829–7710 or 800–344–3860 Toll Free USA/Canada Fax: 480–829–7709 or 800–344–3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800–282–9855 Toll Free USA/Canada

Japan: ON Semiconductor, Japan Customer Focus Center 2–9–1 Kamimeguro, Meguro–ku, Tokyo, Japan 153–0051 Phone: 81–3–5773–3850 ON Semiconductor Website: http://onsemi.com

Order Literature: http://www.onsemi.com/litorder

For additional information, please contact your local Sales Representative.